

Silicon NPN Power Transistors

MJE15032

DESCRIPTION

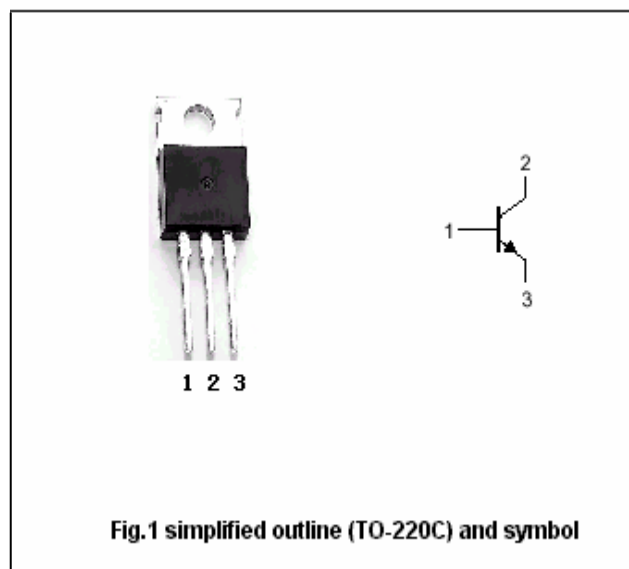
- With TO-220C package
- Complement to type MJE15033
- High transition frequency
- DC current gain specified to 5.0 amperes
 - $h_{FE} = 50$ (Min) @ $I_C = 0.5$ Adc
 - $h_{FE} = 10$ (Min) @ $I_C = 2.0$ Adc

APPLICATIONS

- Designed for use as high-frequency drivers in audio amplifiers.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

ABSOLUTE MAXIMUM RATINGS($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	250	V
V_{CEO}	Collector-emitter voltage	Open base	250	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		8	A
I_{CM}	Collector current-Peak		16	A
I_B	Base current		2	A
P_D	Total power dissipation	$T_a=25^\circ\text{C}$	2	W
		$T_C=25^\circ\text{C}$	50	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{thj-C}	Thermal resistance ; junction to case	2.5	$^\circ\text{C}/\text{W}$
R_{thj-A}	Thermal resistance , junction to ambient	62.5	$^\circ\text{C}/\text{W}$

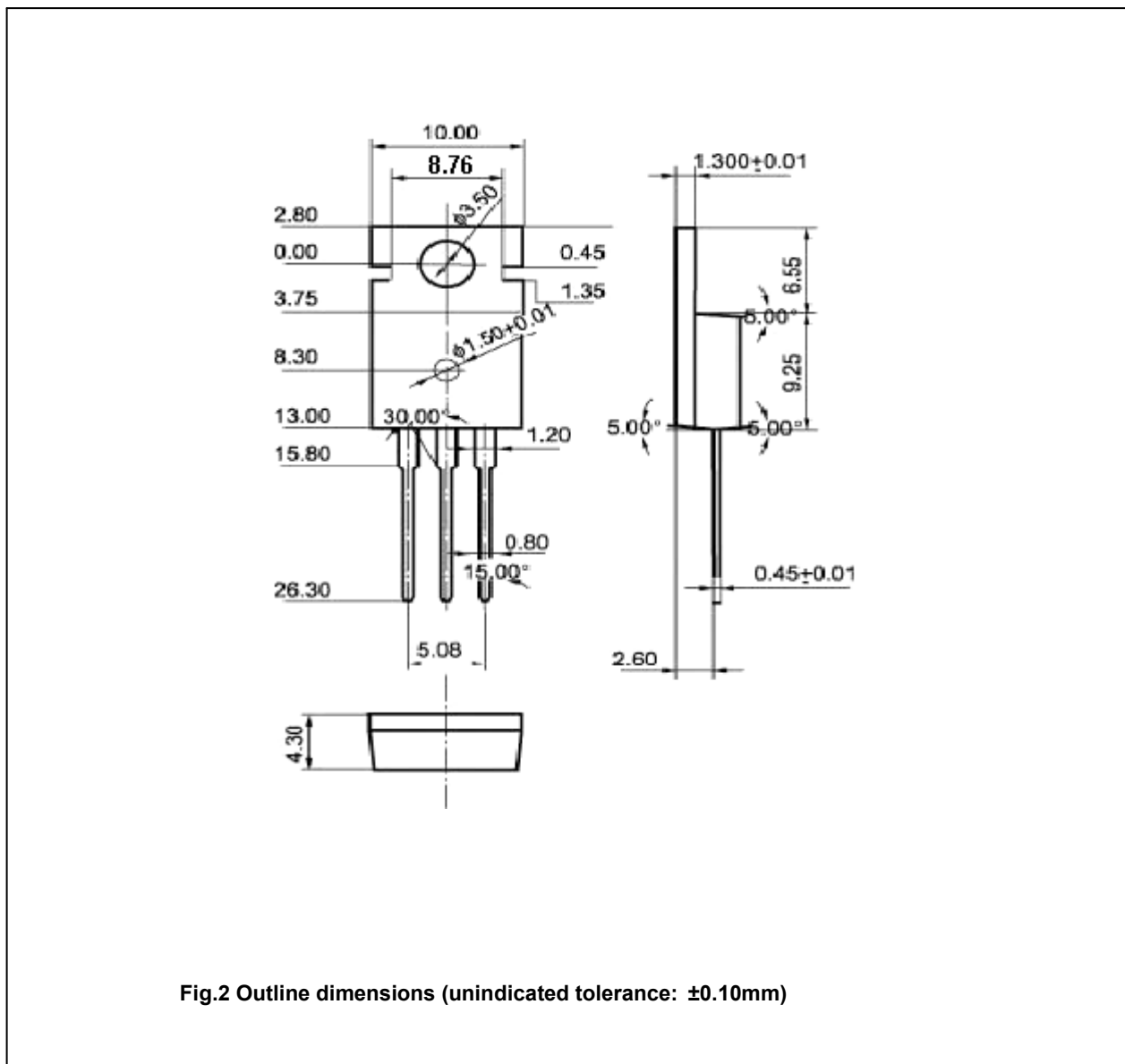
Silicon NPN Power Transistors**MJE15032****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =10mA; I _B =0	250			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =1A; I _B =0.1A			0.5	V
V _{BE}	Base-emitter on voltage	I _C =1A; V _{CE} =5V			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =150V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =0.5A; V _{CE} =5V	50			
h _{FE-2}	DC current gain	I _C =1A; V _{CE} =5V	50			
h _{FE-3}	DC current gain	I _C =2A; V _{CE} =5V	10			
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V; f=1.0MHz	30			MHz

Silicon NPN Power Transistors

MJE15032

PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)